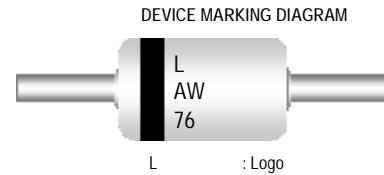


500 mW DO-35 Hermetically Sealed Glass Fast Switching Diodes


 AXIAL LEAD
DO35


Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
P_D	Power Dissipation	500	mW
T_{STG}	Storage Temperature Range	-65 to +150	°C
T_J	Operating Junction Temperature	+150	°C
W_{IV}	Working Inverse Voltage	75	V
I_o	Average Rectified Current	150	mA
I_{FM}	Non-repetitive Peak Forward Current	450	mA
I_{FSURGE}	Peak Forward Surge Current (Pulse Width = 1.0 μs)	2	A

These ratings are limiting values above which the serviceability of the diode may be impaired.

Specification Features:

- § Fast Switching Device ($T_{RR} < 4.0 \text{ nS}$)
- § DO-35 Package (JEDEC)
- § Through-Hole Device Type Mounting
- § Hermetically Sealed Glass
- § Compression Bonded Construction
- § All External Surfaces Are Corrosion Resistant And Leads Are Readily Solderable
- § RoHS Compliant
- § Solder Hot Dip Tin (Sn) Terminal Finish
- § Cathode Indicated By Polarity Band



ELECTRICAL SYMBOL

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Limits		Unit
			Min	Max	
B_V	Breakdown Voltage	$I_R=5\mu\text{A}$	75		Volts
I_R	Reverse Leakage Current	$V_R=50\text{V}$ $V_R=50\text{V} T_A = 150^\circ$		100 100	nA uA
V_F	Forward Voltage	$I_F=100\text{mA}$		1.0	Volts
T_{RR}	Reverse Recovery Time	$I_F=I_R=10\text{mA}, R_L=100\Omega, I_{RR}=1\text{mA}$ $I_F= 10\text{mA}, V_R=6\text{V}, R_L=100\Omega, I_{RR}=1\text{mA}$		4 2	nS
C	Capacitance	$V_R=0\text{V}, f=1\text{MHz}$		4	pF

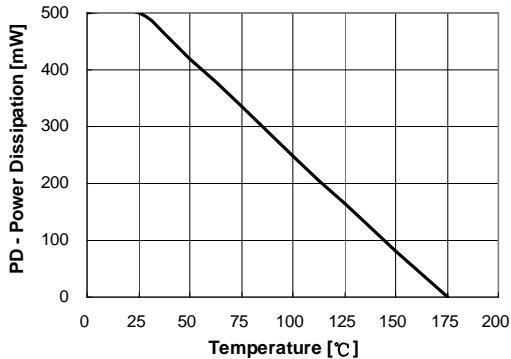
Typical Characteristics


Figure 1. Power Dissipation vs Ambient Temperature
Valid provided leads at a distance of 0.8mm from case are kept at ambient temperature

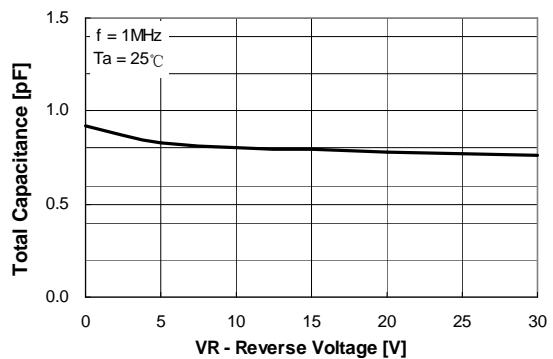


Figure 2. Total Capacitance

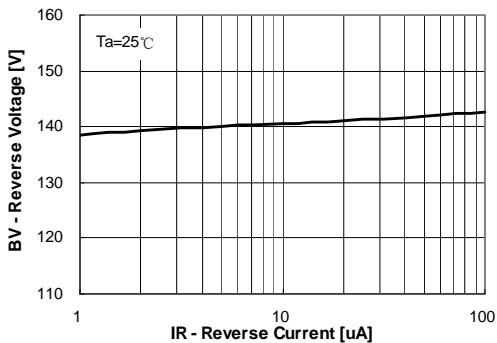


Figure 3. Reverse Voltage vs Reverse Current
BV – 1.0uA to 100uA

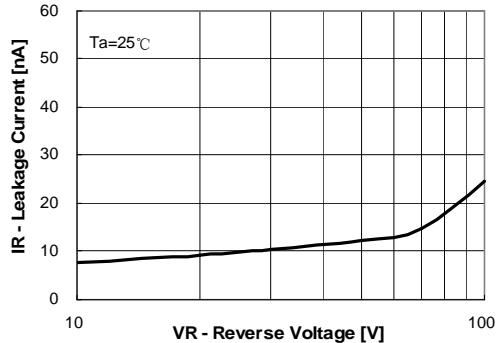


Figure 4. Reverse Current vs Reverse Voltage
IR – 10V to 100V

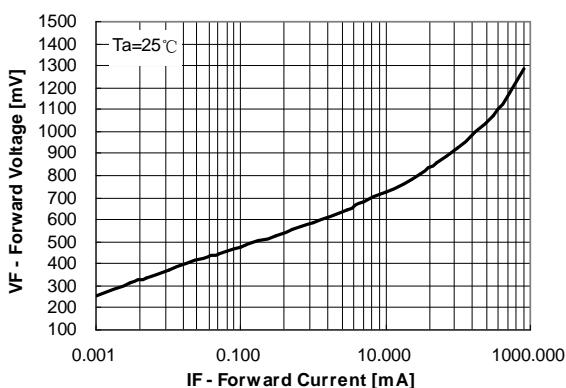


Figure 5. Forward Voltage vs Forward Current
VF – 0.001mA to 800mA

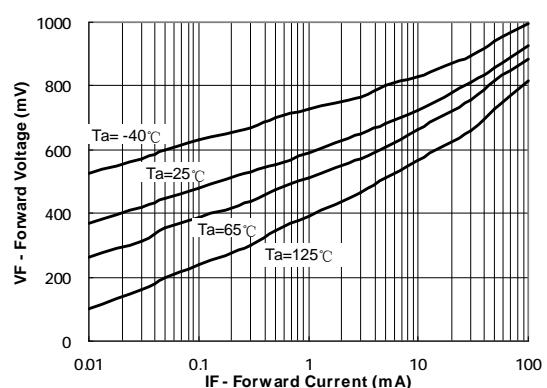


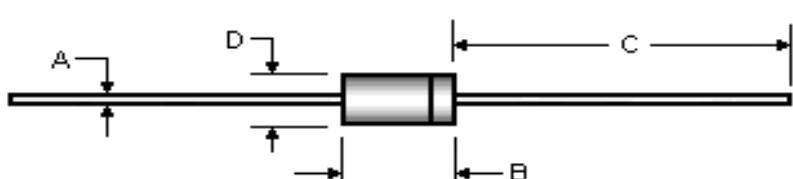
Figure 6. Forward Voltage vs Ambient Temperature
VF – 0.01mA to 100mA (-40 to +125 Deg C)



TAK CHEONG®

SEMICONDUCTOR

Package Outline

Package	Case Outline				
DO-35					
	DO-35				
	DIM	Millimeters		Inches	
		Min	Max	Min	Max
	A	0.46	0.55	0.018	0.022
	B	---	5.08	---	0.200
C	25.40	38.10	1.000	1.500	
D	1.53	2.28	0.060	0.090	

Notes:

1. All dimensions are within JEDEC standard.
2. DO35 polarity denoted by cathode band.